

SGL50N60RUF

Short Circuit Rated IGBT

General Description

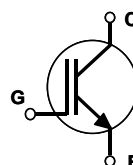
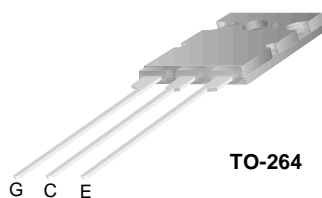
Fairchild's RUF series of Insulated Gate Bipolar Transistors (IGBTs) provide low conduction and switching losses as well as short circuit ruggedness. The RUF series is designed for applications such as motor control, uninterrupted power supplies (UPS) and general inverters where short circuit ruggedness is a required feature.

Features

- Short circuit rated 10us @ $T_C = 100^\circ\text{C}$, $V_{GE} = 15\text{V}$
- High speed switching
- Low saturation voltage : $V_{CE(sat)} = 2.2\text{V}$ @ $I_C = 50\text{A}$
- High input impedance

Applications

AC & DC motor controls, general purpose inverters, robotics, and servo controls.



Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Description | SGL50N60RUF | Units |
|-------------|---|-------------|------------------|
| V_{CES} | Collector-Emitter Voltage | 600 | V |
| V_{GES} | Gate-Emitter Voltage | ± 20 | V |
| I_C | Collector Current @ $T_C = 25^\circ\text{C}$ | 80 | A |
| | Collector Current @ $T_C = 100^\circ\text{C}$ | 50 | A |
| $I_{CM(1)}$ | Pulsed Collector Current | 150 | A |
| T_{SC} | Short Circuit Withstand Time @ $T_C = 100^\circ\text{C}$ | 10 | us |
| P_D | Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ | 250 | W |
| | Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$ | 100 | W |
| T_J | Operating Junction Temperature | -55 to +150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature Range | -55 to +150 | $^\circ\text{C}$ |
| T_L | Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds | 300 | $^\circ\text{C}$ |

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

| Symbol | Parameter | Typ. | Max. | Units |
|-----------------|---|------|------|--------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case | -- | 0.5 | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | -- | 25 | $^\circ\text{C/W}$ |

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---|--|---|--|------|-------|-------|
| Off Characteristics | | | | | | |
| BV _{CES} | Collector-Emitter Breakdown Voltage | V _{GE} = 0V, I _C = 250uA | 600 | -- | -- | V |
| ΔB _V CES/ ΔT _J | Temperature Coefficient of Breakdown Voltage | V _{GE} = 0V, I _C = 1mA | -- | 0.6 | -- | V/°C |
| I _{CES} | Collector Cut-Off Current | V _{CE} = V _{CES} , V _{GE} = 0V | -- | -- | 250 | uA |
| I _{GES} | G-E Leakage Current | V _{GE} = V _{GES} , V _{CE} = 0V | -- | -- | ± 100 | nA |
| On Characteristics | | | | | | |
| V _{GE(th)} | G-E Threshold Voltage | I _C = 50mA, V _{CE} = V _{GE} | 5.0 | 6.0 | 8.5 | V |
| V _{CE(sat)} | Collector to Emitter Saturation Voltage | I _C = 50A, V _{GE} = 15V | -- | 2.2 | 2.8 | V |
| | | I _C = 80A, V _{GE} = 15V | -- | 2.5 | -- | V |
| Dynamic Characteristics | | | | | | |
| C _{ies} | Input Capacitance | V _{CE} =30V, V _{GE} = 0V, f = 1MHz | -- | 3311 | -- | pF |
| C _{oes} | Output Capacitance | | -- | 399 | -- | pF |
| C _{res} | Reverse Transfer Capacitance | | -- | 139 | -- | pF |
| Switching Characteristics | | | | | | |
| t _{d(on)} | Turn-On Delay Time | V _{CC} = 300 V, I _C = 50A, R _G = 5.9Ω, V _{GE} = 15V, Inductive Load, T _C = 25°C | -- | 26 | -- | ns |
| t _r | Rise Time | | -- | 89 | -- | ns |
| t _{d(off)} | Turn-Off Delay Time | | -- | 66 | 100 | ns |
| t _f | Fall Time | | -- | 118 | 200 | ns |
| E _{on} | Turn-On Switching Loss | | -- | 1.68 | -- | mJ |
| E _{off} | Turn-Off Switching Loss | | -- | 1.03 | -- | mJ |
| E _{ts} | Total Switching Loss | V _{CC} = 300 V, I _C = 50A, R _G = 5.9Ω, V _{GE} = 15V, Inductive Load, T _C = 125°C | -- | 2.71 | 3.8 | mJ |
| t _{d(on)} | Turn-On Delay Time | | -- | 28 | -- | ns |
| t _r | Rise Time | | -- | 91 | -- | ns |
| t _{d(off)} | Turn-Off Delay Time | | -- | 68 | 110 | ns |
| t _f | Fall Time | | -- | 261 | 400 | ns |
| E _{on} | Turn-On Switching Loss | | -- | 1.7 | -- | mJ |
| E _{off} | Turn-Off Switching Loss | | -- | 2.31 | -- | mJ |
| E _{ts} | Total Switching Loss | | -- | 4.01 | 5.62 | mJ |
| T _{sc} | Short Circuit Withstand Time | | V _{CC} = 300 V, V _{GE} = 15V, @ T _C = 100°C | 10 | -- | -- |
| Q _g | Total Gate Charge | V _{CE} = 300 V, I _C = 50A, V _{GE} = 15V | -- | 145 | 210 | nC |
| Q _{ge} | Gate-Emitter Charge | | -- | 25 | 35 | nC |
| Q _{gc} | Gate-Collector Charge | | -- | 70 | 100 | nC |
| L _e | Internal Emitter Inductance | Measured 5mm from PKG | -- | 18 | -- | nH |

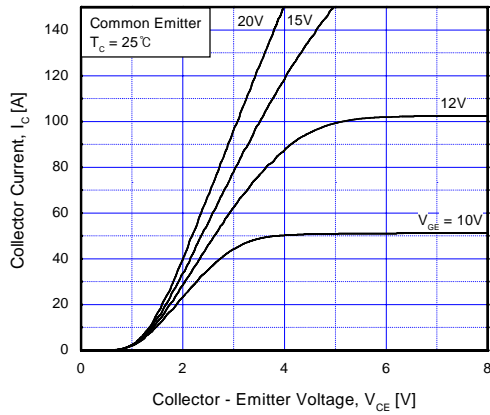


Fig 1. Typical Output Characteristics

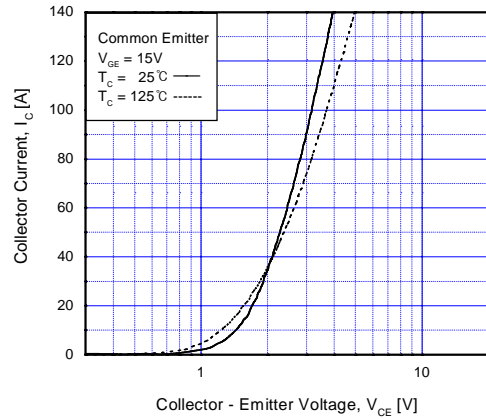


Fig 2. Typical Saturation Voltage Characteristics

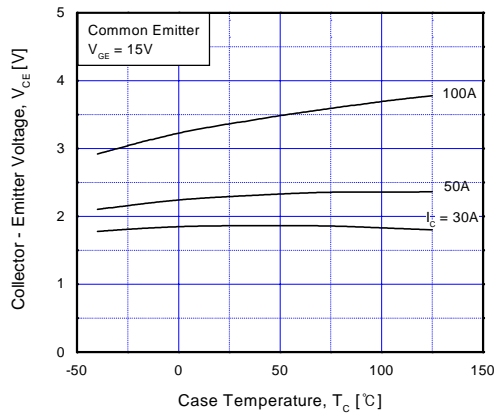


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

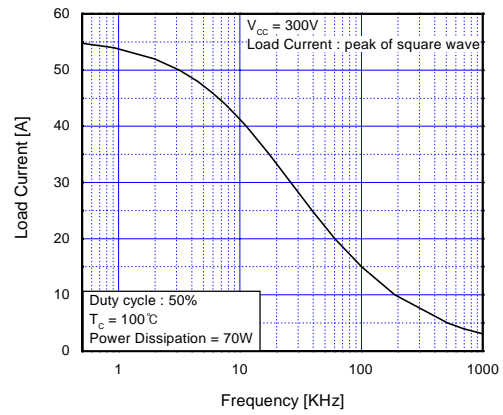


Fig 4. Load Current vs. Frequency

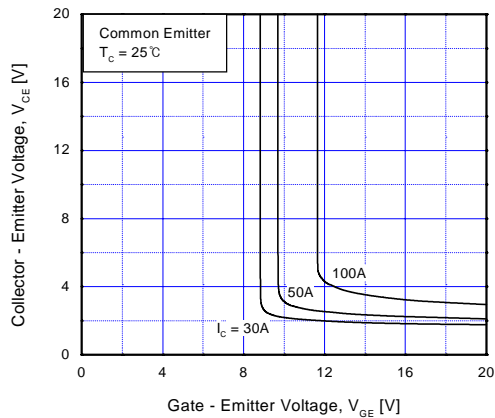


Fig 5. Saturation Voltage vs. V_{GE}

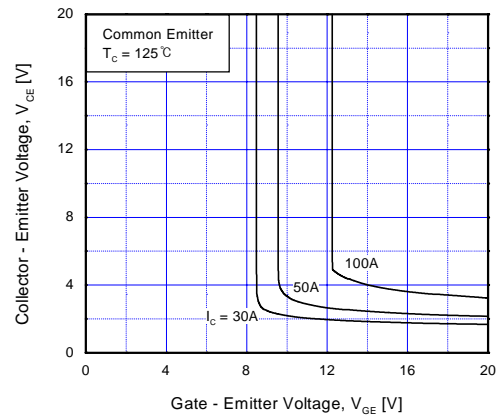


Fig 6. Saturation Voltage vs. V_{GE}

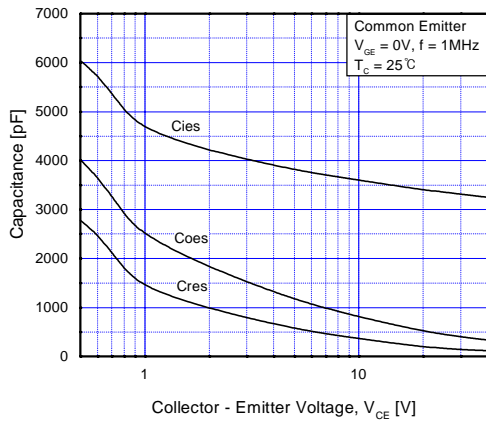


Fig 7. Capacitance Characteristics

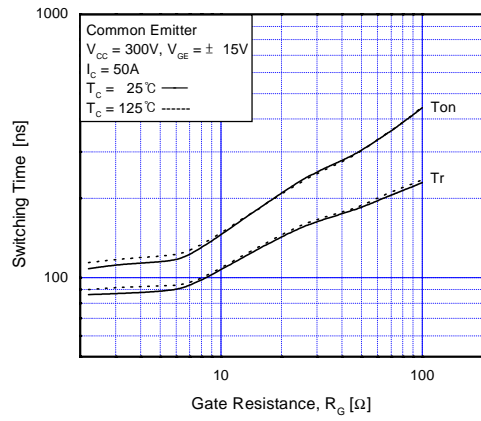


Fig 8. Turn-On Characteristics vs. Gate Resistance

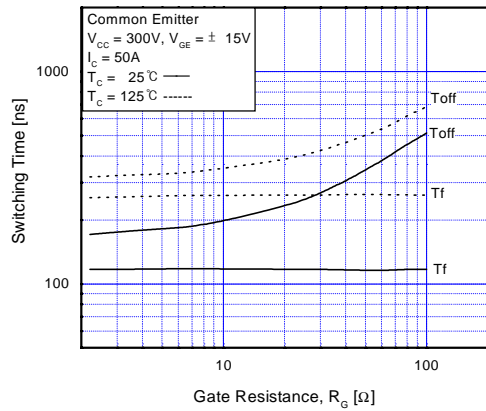


Fig 9. Turn-Off Characteristics vs. Gate Resistance

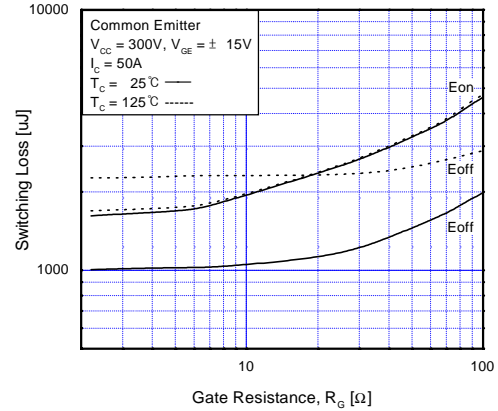


Fig 10. Switching Loss vs. Gate Resistance

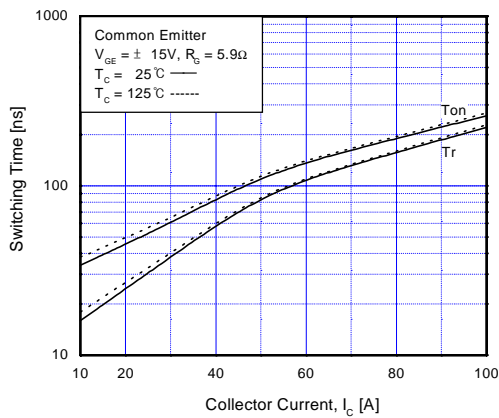


Fig 11. Turn-On Characteristics vs. Collector Current

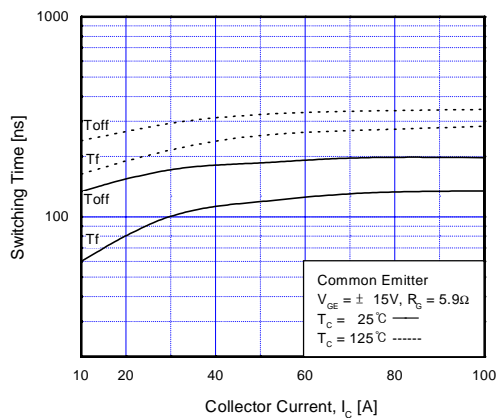


Fig 12. Turn-Off Characteristics vs. Collector Current

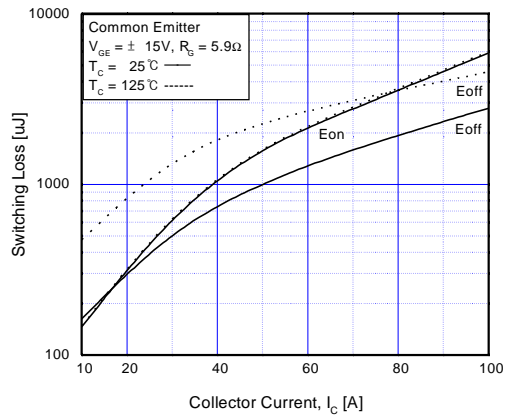


Fig 13. Switching Loss vs. Collector Current

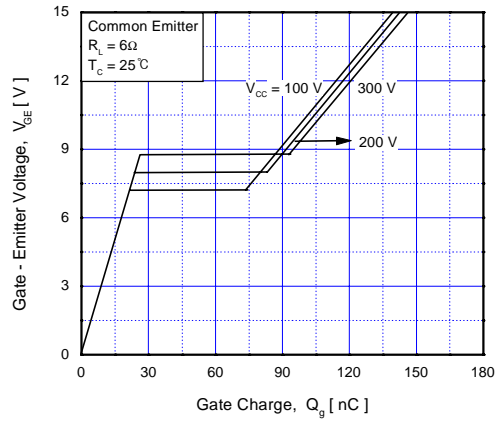


Fig 14. Gate Charge Characteristics

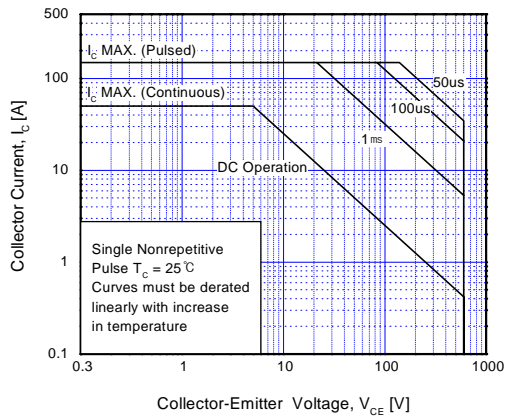


Fig 15. SOA Characteristics

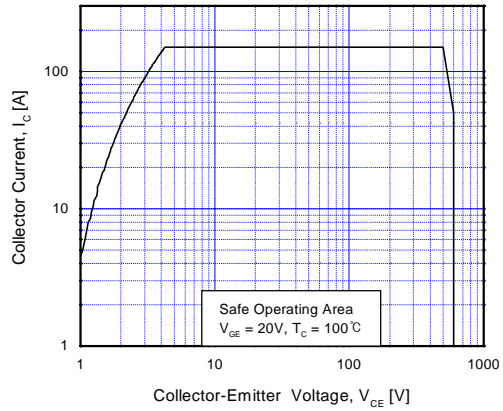


Fig 16. Turn-Off SOA Characteristics

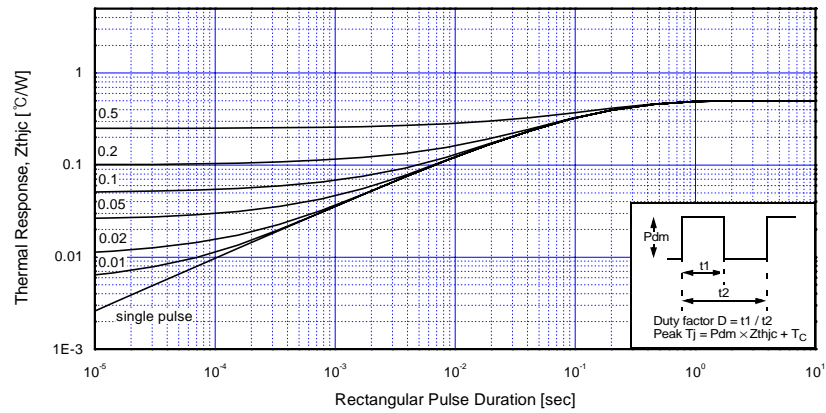


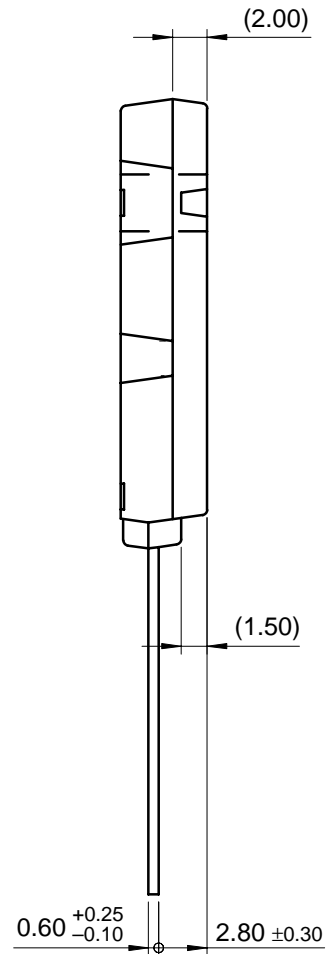
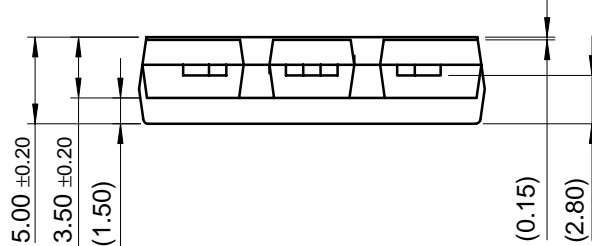
Fig 17. Transient Thermal Impedance of IGBT

SGL50N60RUF

Technical drawing of a mechanical part, likely a bracket or base plate, showing top and side views with dimensions in millimeters. The top view shows a rectangular plate with a central circular hole ($\varnothing 3.30 \pm 0.20$) and four corner holes (R1.00 and R2.00). The side view shows the thickness of the plate (2.50 ± 0.10) and the height of the mounting holes (1.50). Dimensions are given in millimeters, with tolerances indicated by \pm symbols.

Key dimensions and tolerances:

- Overall width: 20.00 ± 0.20
- Overall height: 20.00 ± 0.20
- Central hole diameter: $\varnothing 3.30 \pm 0.20$
- Corner hole radii: R1.00 and R2.00
- Mounting hole height: 1.50
- Plate thickness: 2.50 ± 0.10
- Bottom flange width: 5.45 TYP with tolerance $[5.45 \pm 0.30]$



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SGL50N60RUF Rev. A1

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